

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}TYP$	I_D
100V	70m Ω @10V	7A
	85m Ω @4.5V	

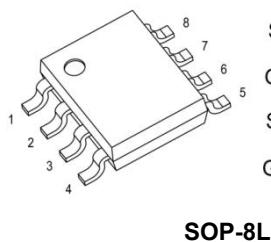
Feature

- Low on-resistance
- Fast Switching

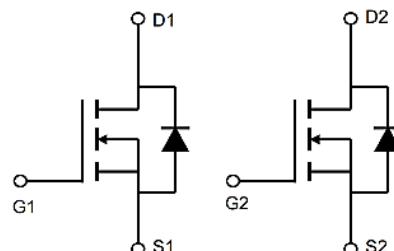
Application

- Synchronous Rectifier
- Primary Switch For Bridge Topology

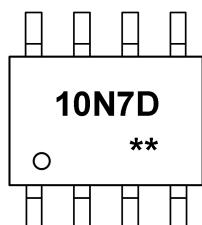
Package



Circuit diagram



Marking



10N7D : Product code
 ** : Week code.

Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current, V _{GS} @ 10V ¹	I _D	7	A
Pulsed Drain Current ²	I _{DM}	28	A
Total Power Dissipation	P _D	2.5	W
Thermal Resistance Junction-ambient ¹	R _{θJA}	50	°C/W
Storage Temperature Range	T _{STG}	-55 to 150	°C
Operating Junction Temperature Range	T _J	-55 to 150	°C

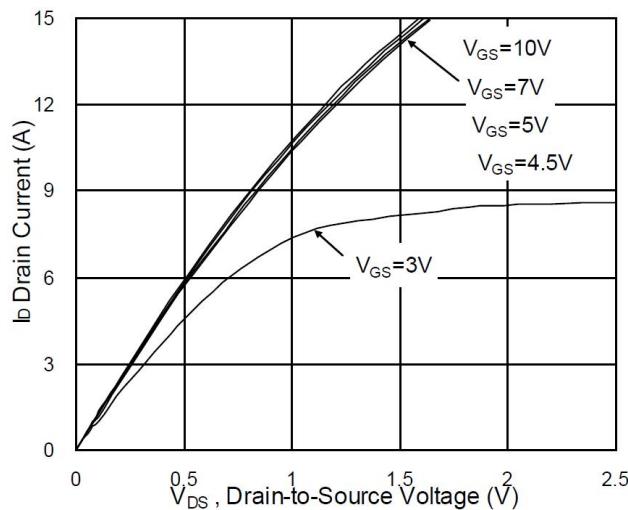
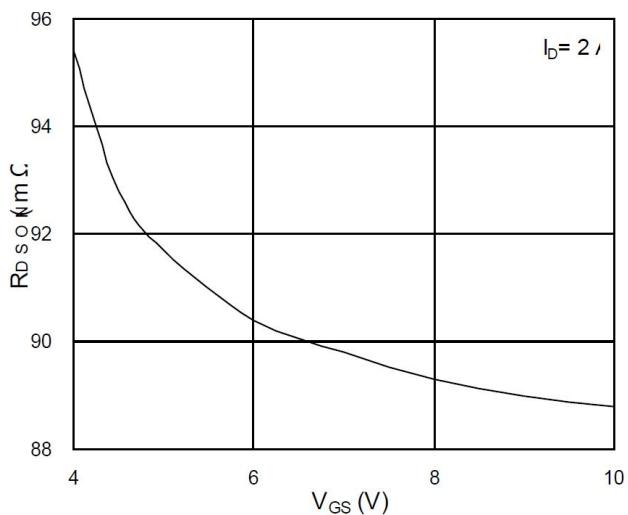
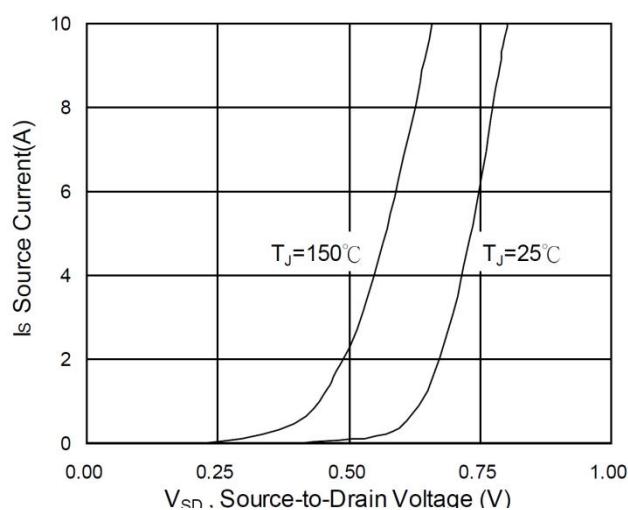
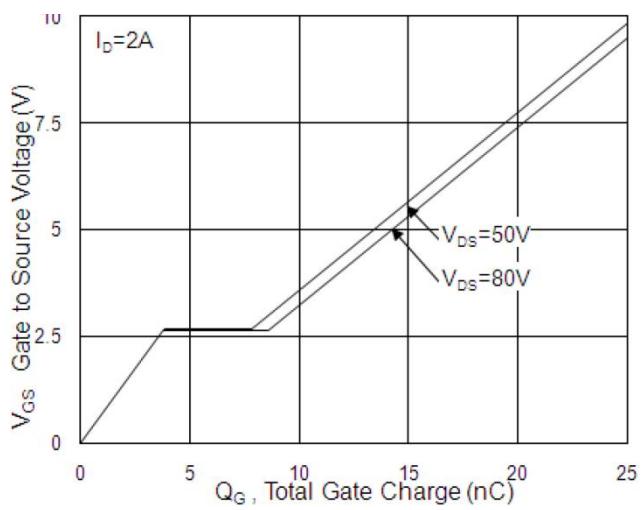
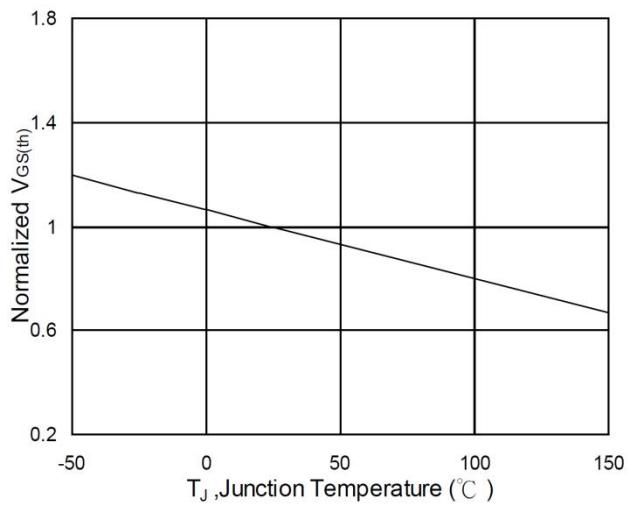
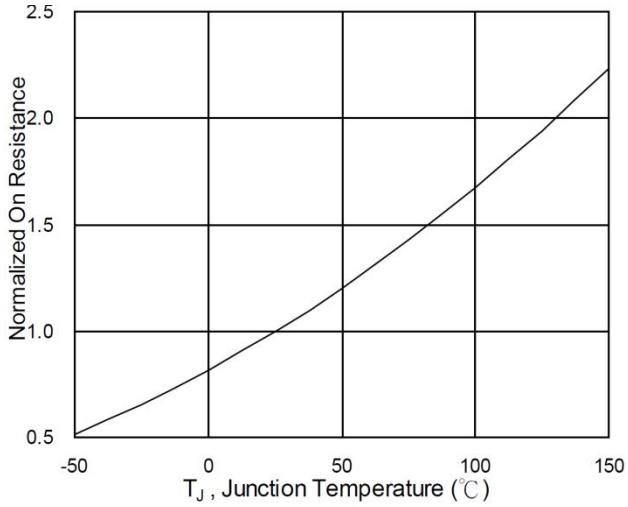
Electrical characteristics (T_A=25 °C, unless otherwise noted)

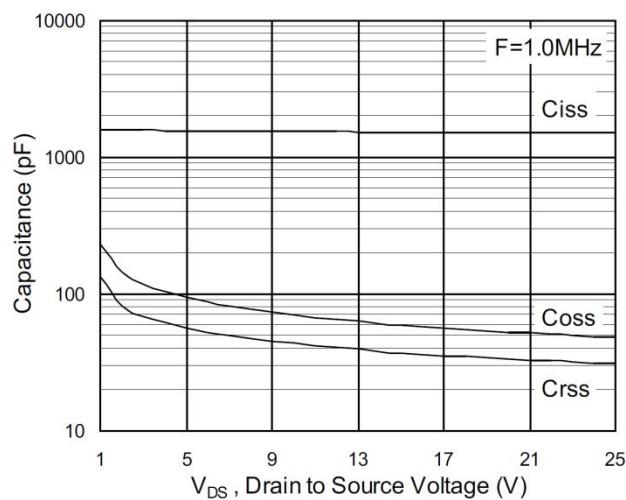
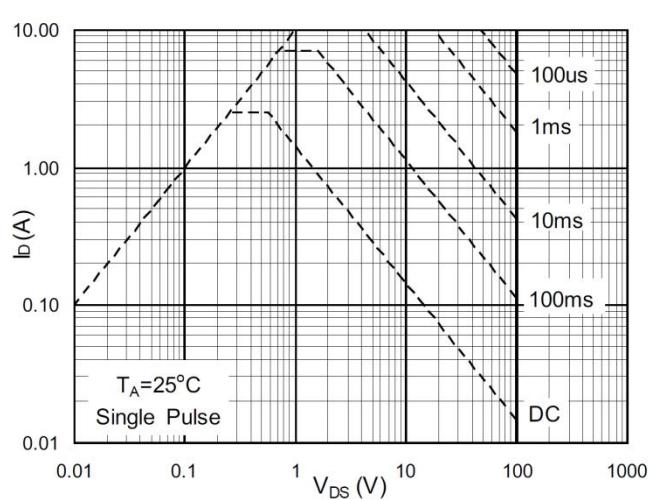
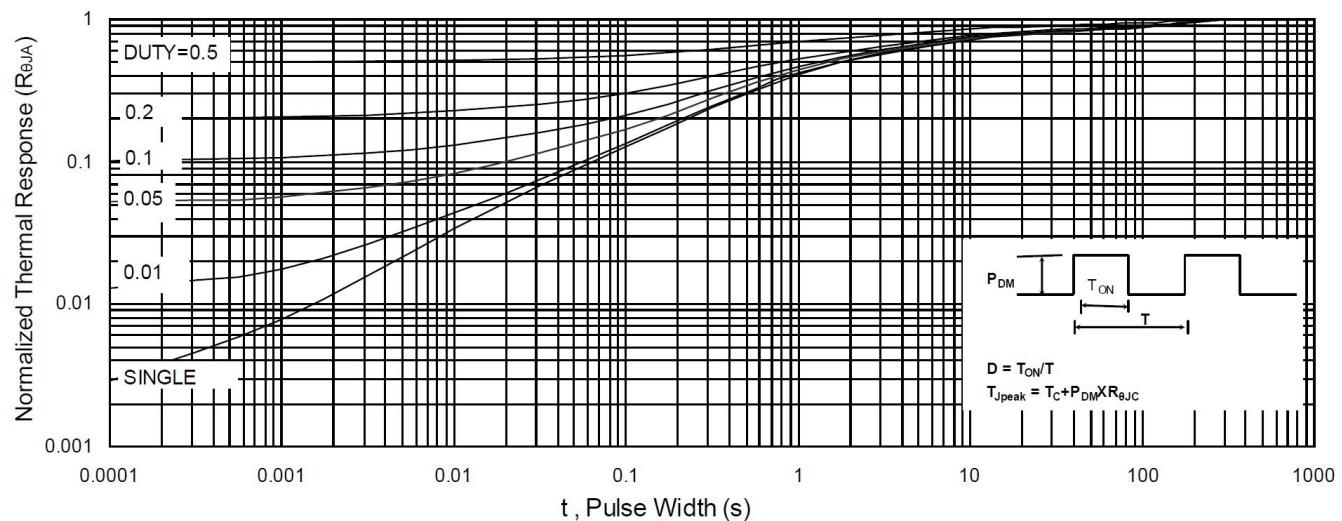
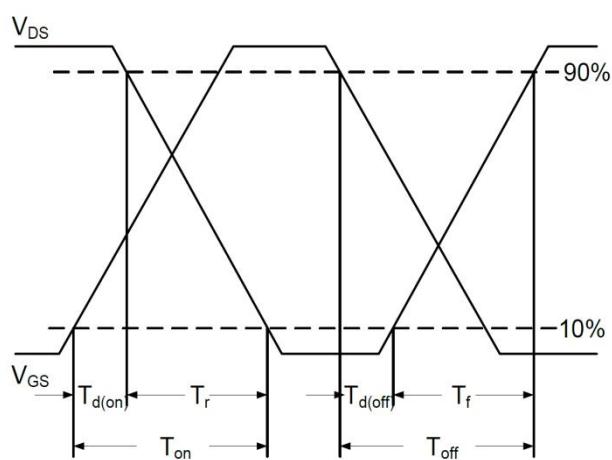
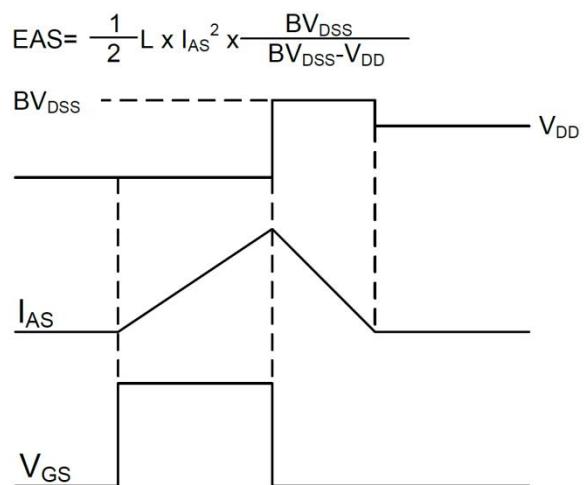
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V , ID=250uA	100			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =80V , V _{GS} =0V , T _J =25°C			1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V , V _{DS} =0V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{GS} =V _{DS} , ID =250uA	1.2	1.8	2.5	V
Static Drain-Source On-Resistance ²	R _{DS(ON)}	V _{GS} =10V , ID=2A		70	100	mΩ
		V _{GS} =4.5V , ID=1A		85	110	
Dynamic Characteristics						
Total Gate Charge (10V)	Q _g	V _{DS} =80V , V _{GS} =10V , ID=2A		26.2	36.7	nC
Gate-Source Charge	Q _{gs}			3.8	5.32	
Gate-Drain Charge	Q _{gd}			4.8	6.7	
Input Capacitance	C _{iss}	V _{DS} =15V , V _{GS} =0V , f=1MHz		1535	2149	pF
Output Capacitance	C _{oss}			60	84	
Reverse Transfer Capacitance	C _{rss}			37	52	
Switching Characteristics						
Turn-On Delay Time	T _{d(on)}	VDD=50V , V _{GS} =10V , RG=3.3Ω ID=2A		4.2	8.4	ns
Rise Time	T _r			7.6	14	
Turn-Off Delay Time	T _{d(off)}			41	82	
Fall Time	T _f			14	28	
Drain-Source Diode Characteristics						
Continuous Source Current ^{1,4}	I _S	VG=VD=0V , Force Current			2.5	A
Pulsed Source Current ^{2,4}	I _{SM}				10	A
Diode Forward Voltage ²	V _{SD}	V _{GS} =0V , IS=1A , T _J =25°C			1.2	V
Reverse Recovery Time	t _{rr}	IF=2A , dI/dt=100A/μs , T _J =25°C		35		nS
Reverse Recovery Charge	Q _{rr}			17		nC

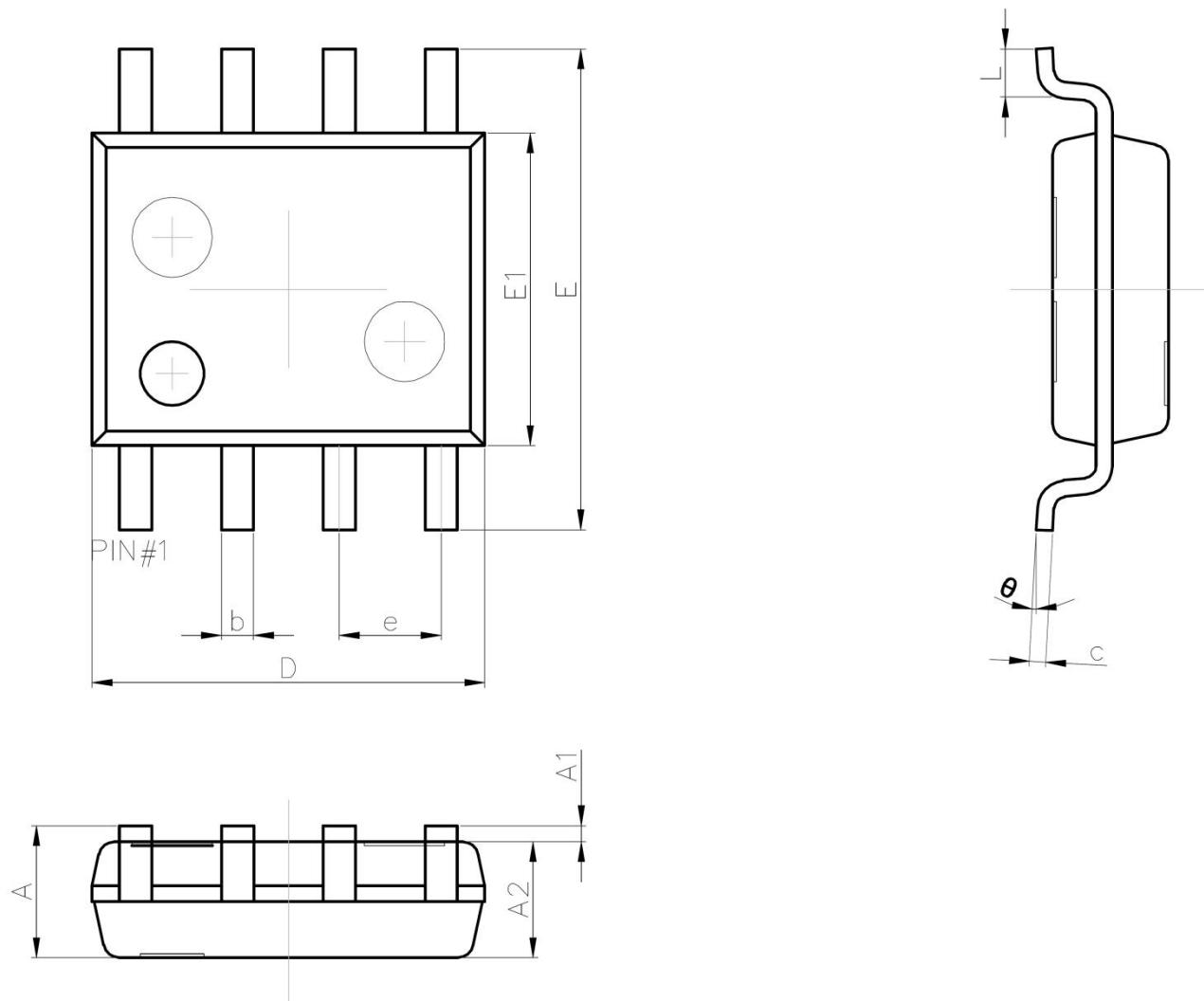
Note:

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
2. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
3. The power dissipation is limited by 150°C junction temperature
4. The data is theoretically the same as ID and IDM, in real applications, should be limited by total power dissipation.

Typical Characteristics


Typical Output Characteristics

On-Resistance vs. Gate-Source

Forward Characteristics Of Reverse

Gate-Charge Characteristics

Normalized $V_{GS(th)}$ vs. T_J

Normalized $R_{DS(on)}$ vs. T_J


Capacitance

Safe Operating Area

Normalized Maximum Transient Thermal Impedance

Switching Time Waveform

Unclamped Inductive Switching Waveform

SOP-8 Package Information


Symbol	Dimensions In Millimeters	
	Min.	Max.
A	1.35	1.75
A1	0.10	0.25
A2	1.35	1.55
b	0.33	0.51
c	0.17	0.25
D	4.80	5.00
e	1.27 REF.	
E	5.80	6.20
E1	3.80	4.00
L	0.40	1.27
θ	0°	8°

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